Vishay Semiconductors

ROHS COMPLIANT

HALOGEN

FREE

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Hyperfast Rectifier, 30 A FRED Pt®



LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS								
I _{F(AV)} 30 A								
V _R	600 V							
V _F at I _F	1.40 V							
t _{rr} (typ.)	22 ns							
T _J max.	175 °C							
Package	TO-3PF							
Circuit configuration	Common anode							

FEATURES

- Hyperfast soft recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- Fully isolated package (V_{INS} = 2500 V_{RMS})
- Designed and qualified according to JEDEC[®]-JESD 47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

Hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of switch mode power supplies and inverters (air conditioning, high-frequency welding, UPS, and motor drives)

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

MECHANICAL DATA

Case: TO-3PF

Molding compound meets UL 94 V-0 flammability rating **Terminals:** matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Peak repetitive reverse voltage	V _{RRM}		600	V				
Average rectified forward current in DC	I _{F(AV)}		30	^				
Non-repetitive peak surge current	I _{FSM}	$T_J = 25$ °C, both anodes connection	280	A				
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +175	°C				

ELECTRICAL SPECIFICATIONS (T _J = 25 $^{\circ}$ C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-	v	
Forward voltage	V	I _F = 30 A	- 1.70 2.				
Forward voltage	V _F	I _F = 30 A, T _J = 150 °C	-	1.40	1.65		
	1	$V_{\rm R} = V_{\rm R}$ rated	-	0.02	10		
Reverse leakage current	IR	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	- 36 300	μA			
Junction capacitance	CT	V _R = 600 V	-	19	-	pF	

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VS-AZH3106FP-M3



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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25 \text{ °C}$ unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS			
			$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 100 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$			-			
Reverse recovery time	t _{rr}	T _J = 25 °C		-	90	-	ns		
		T _J = 125 °C		-	110	-			
Deels receivers ourrent	1	T _J = 25 °C	I _F = 30 A, dI _F /dt = 200 A/μs,	-	4.1	-	A nC		
Peak recovery current	I _{RRM}	T _J = 125 °C	$V_{\rm B} = 400 \text{ V}$	-	9.4	-			
	Q _{rr}	T _J = 25 °C		-	230	-			
Reverse recovery charge		T _J = 125 °C		-	730	-			

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	L TEST CONDITIONS MIN. TYP.				UNITS		
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C		
Thermal resistance, junction-to-case	R _{thJC}		-	2.30	2.90			
Thermal resistance, junction-to-ambient	R _{thJA}	Typical socket mount		30	-	°C/W		
Typical thermal resistance, case-to-heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.5	-			
Weight			-	6.2	-	g		
Weight			-	0.21	-	oz.		
Mounting torque				6 (5.3)	kgf · cm (lbf · in)			
Marking device		Case style TO-3PF	AZH3106FP					



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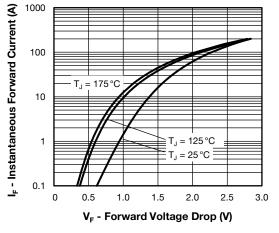


Fig. 1 - Forward Voltage Drop Characteristics

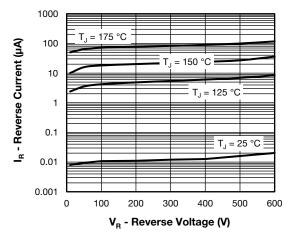


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

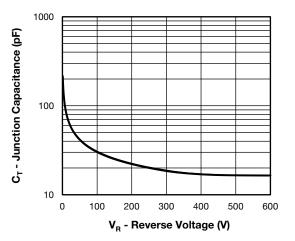


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

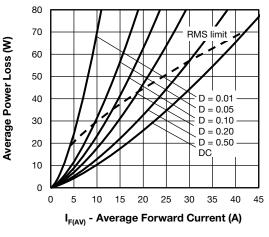
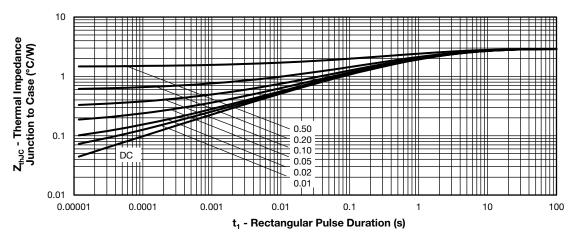
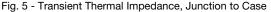


Fig. 4 - Forward Power Loss Characteristics





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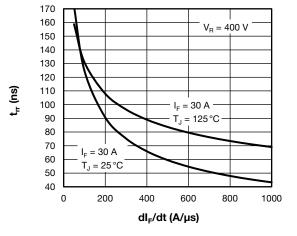


Fig. 6 - Typical Reverse Recovery Time vs. dl_F/dt

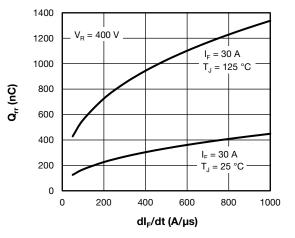


Fig. 7 - Typical Reverse Recovery Charge vs. dl_F/dt

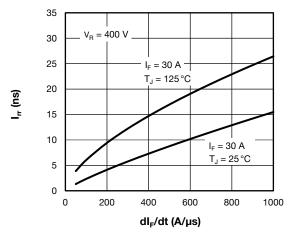


Fig. 8 - Typical Reverse Recovery Current vs. dl_F/dt



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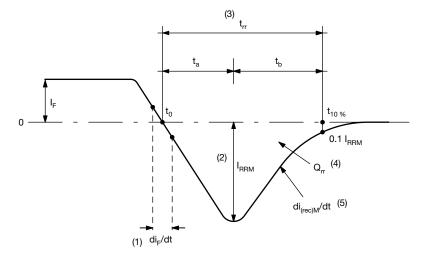


Fig. 9 - Reverse Recovery Waveform and Definitions

Notes

- $^{(1)}$ di_F/dt rate of change of current through zero crossing
- $^{(2)}$ I_{RRM} peak reverse recovery current
- $^{(3)}$ t_{rr} reverse recovery time measured from t₀, crossing point of negative going I_F, to point t_{10%}, 0.1 I_{RRM}
- $^{(4)}$ $\, \dot{Q}_{rr}$ area under curve defined by t_0 and $t_{10~\%}$

$$Q_{rr} = \int_{t_0}^{t_{10\%}} I(t) dt$$

 $^{(5)}$ di_{(rec)}M/dt - peak rate of change of current during t_b portion of t_{rr}

ORDERING INFORMATION TABLE

Device code

e code	vs-	Α	z	н	31	06	FP	-M3		
		(2)	(3)	4	5	6	(7)	(8)		
	1 · 2 ·		nay Sem cuit conf		•	oduct				
	3 -	A =	single c	liode, de	ouble ar	node				
	4 -	• H =	Z = TO-3FP package H = hyperfast recovery time Current code: 31 = 30 A							
	5 - 6 -	· Volt	age coo	de: 06 =						
	7 - 8 -		= FullPA ironmer		:					
		-M3	3 = halog	gen-free	, RoHS	-compli	ant, and	d termin		

LINKS TO RELATED DOCUMENTS						
Dimensions www.vishay.com/doc?96691						
Part marking information	www.vishay.com/doc?96690					

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